GTL2007

12-bit GTL to LVTTL translator with power good control

Rev. 02 — 16 February 2007 Product data sheet

1. General description

The GTL2007 is a customized translator between dual Xeon processors, Platform Health Management, South Bridge and Power Supply LVTTL and GTL signals.

The GTL2007 is derived from the GTL2006 with an enable function added that disables the error output to the monitoring agent for platforms that monitor the individual error conditions from each processor. This enable function can be used so that false error conditions are not passed to the monitoring agent when the system is unexpectedly powered down. This unexpected power-down could be from a power supply overload, a CPU thermal trip, or some other event of which the monitoring agent is unaware.

A typical implementation would be to connect each enable line to the system power good signal or the individual enables to the VRD power good for each processor.

Typically Xeon processors specify a V_{TT} of 1.1 V to 1.2 V, as well as a nominal V_{ref} of 0.73 V to 0.76 V. To allow for future voltage level changes that may extend V_{ref} to 0.63 of V_{TT} (minimum of 0.693 V with V_{TT} of 1.1 V) the GTL2007 allows a minimum V_{ref} of 0.66 V. Characterization results show that there is little DC or AC performance variation between these V_{ref} levels.

2. Features

- Operates as a GTL to LVTTL sampling receiver or LVTTL to GTL driver
- Operates at GTL–/GTL/GTL+ signal levels
- EN1 and EN2 disable error output
- 3.0 V to 3.6 V operation
- LVTTL I/O not 5 V tolerant
- Series termination on the LVTTL outputs of 30 Ω
- ESD protection exceeds 2000 V HBM per JESD22-A114, 200 V MM per JESD22-A115, and 1000 V CDM per JESD22-C101
- Latch-up testing is done to JEDEC Standard JESD78 which exceeds 500 mA
- Package offered: TSSOP28

3. Quick reference data

Table 1. Quick reference data

T_{amb} = 25 °C.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{io}	input/output capacitance	A port; V_O = 3.0 V or 0 V	-	2.5	3.5	pF
		B port; V_O = V_{TT} or 0 V	-	1.5	2.5	pF
V_{ref} = 0.73 V; V_{TT} = 1.1 V						
t_{PLH}	LOW-to-HIGH propagation delay	nA to nB; see Figure 4	1	4	8	ns
		nBI to nAO; see Figure 5	2	5.5	10	ns
t_{PHL}	HIGH-to-LOW propagation delay	nA to nB; see Figure 4	2	5.5	10	ns
		nBI to nAO; see Figure 5	2	5.5	10	ns
V_{ref} = 0.76 V; V_{TT} = 1.2 V						
t_{PLH}	LOW-to-HIGH propagation delay	nA to nB; see Figure 4	1	4	8	ns
		nBI to nAO; see Figure 5	2	5.5	10	ns
t_{PHL}	HIGH-to-LOW propagation delay	nA to nB; see Figure 4	2	5.5	10	ns
		nBI to nAO; see Figure 5	2	5.5	10	ns

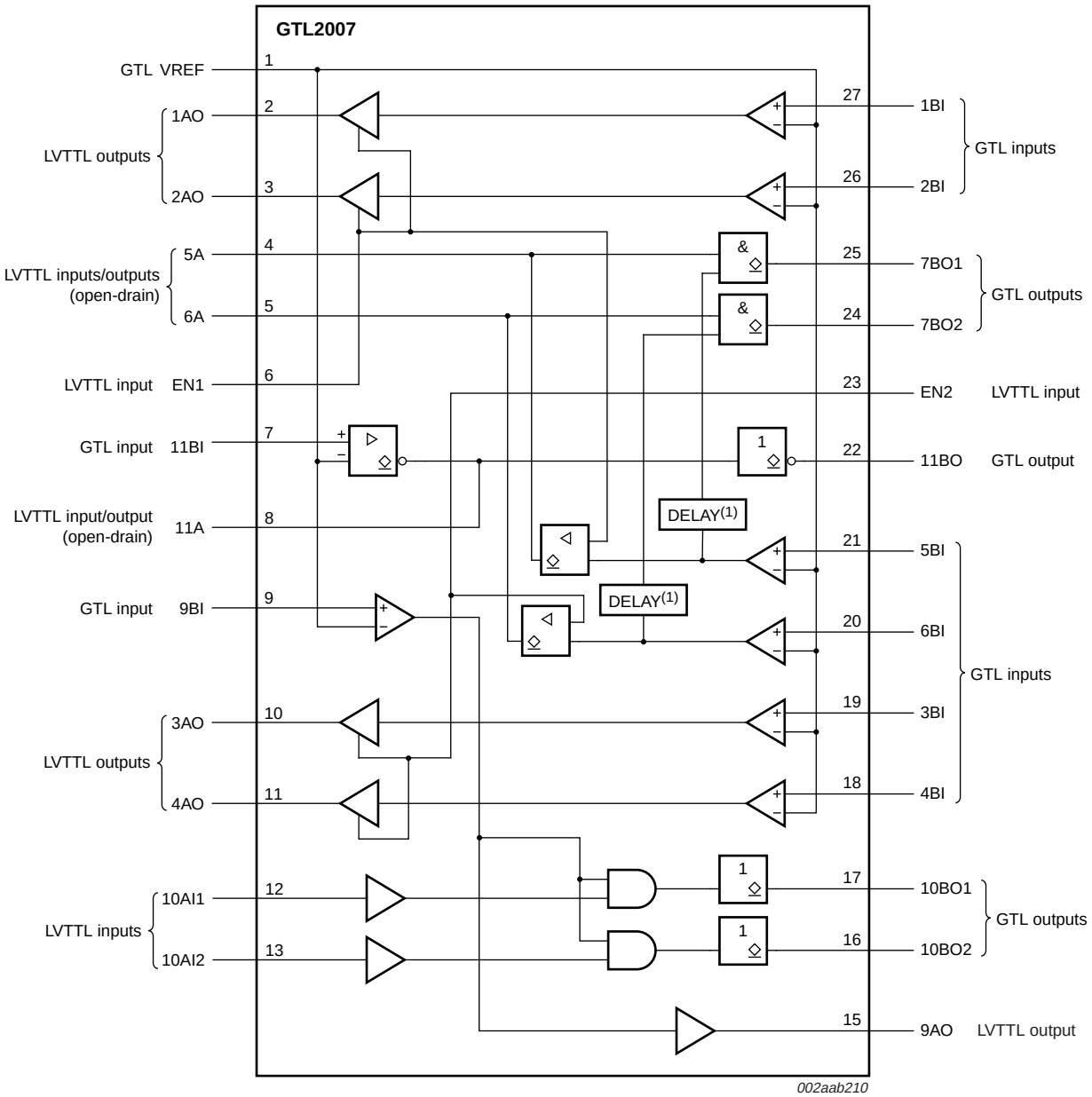
4. Ordering information

Table 2. Ordering information

T_{amb} = −40 °C to +85 °C.

Type number	Topside mark	Package		
		Name	Description	Version
GTL2007PW	GTL2007	TSSOP28	plastic thin shrink small outline package; 28 leads; body width 4.4 mm	SOT361-1

5. Functional diagram



(1) The enable on 7BO1/7BO2 include a delay that prevents the transient condition where 5BI/6BI go from LOW to HIGH, and the LOW to HIGH on 5A/6A lags up to 100 ns from causing a LOW glitch on the 7BO1/7BO2 outputs.

Fig 1. Logic diagram of GTL2007

6. Pinning information

6.1 Pinning

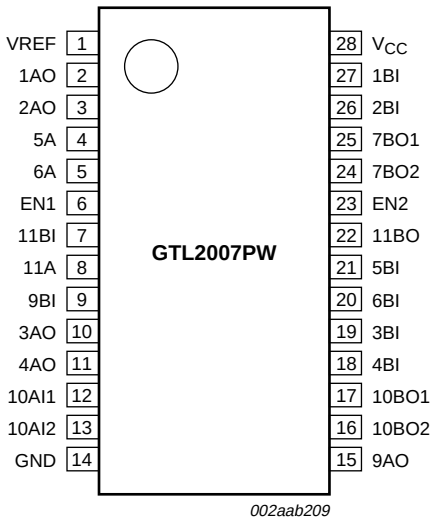


Fig 2. Pin configuration for TSSOP28

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
VREF	1	GTL reference voltage
1AO	2	data output (LVTTL)
2AO	3	data output (LVTTL)
5A	4	data input/output (LVTTL), open-drain
6A	5	data input/output (LVTTL), open-drain
EN1	6	enable input (LVTTL)
11BI	7	data input (GTL)
11A	8	data input/output (LVTTL), open-drain
9BI	9	data input (GTL)
3AO	10	data output (LVTTL)
4AO	11	data output (LVTTL)
10AI1	12	data input (LVTTL)
10AI2	13	data input (LVTTL)
GND	14	ground (0 V)
9AO	15	data output (LVTTL)
10BO2	16	data output (GTL)
10BO1	17	data output (GTL)
4BI	18	data input (GTL)
3BI	19	data input (GTL)

Table 3. Pin description *…continued*

Symbol	Pin	Description
6BI	20	data input (GTL)
5BI	21	data input (GTL)
11BO	22	data output (GTL)
EN2	23	enable input (LVTTL)
7BO2	24	data output (GTL)
7BO1	25	data output (GTL)
2BI	26	data input (GTL)
1BI	27	data input (GTL)
V_{CC}	28	positive supply voltage

7. Functional description

Refer to Figure 1 “Logic diagram of GTL2007”.

7.1 Function tables

Table 4. GTL input signals

H = HIGH voltage level; L = LOW voltage level.

Input	Output[1]
1BI/2BI/3BI/4BI/9BI	**1AO/2AO/3AO/4AO/9AO**
L	L
H	H

[1] 1AO, 2AO, 3AO, 4AO and 5A/6A condition changed by ENn power good signal as described in Table 5 and Table 6.

Table 5. EN1 power good signal

H = HIGH voltage level; L = LOW voltage level.

EN1	1AO and 2AO	5A
L	H	5BI disconnected
H	follows BI	5BI connected

Table 6. EN2 power good signal

H = HIGH voltage level; L = LOW voltage level.

EN2	3AO and 4AO	6A
L	H	6BI disconnected
H	follows BI	6BI connected

Table 7. SMI signals

H = HIGH voltage level; L = LOW voltage level.

Input	Input	Output
10AI1/10AI2	**9BI**	**10BO1/10BO2**
L	L	L
L	H	L
H	L	L
H	H	H

Table 8. PROCHOT signals

H = HIGH voltage level; L = LOW voltage level.

Input	Input/output	Output
5BI/6BI	**5A/6A (open-drain)**	**7BO1/7BO2**
L	L	H[1]
H	L[2]	L
H	H	H

[1] The enable on 7BO1/7BO2 includes a delay that prevents the transient condition where 5BI/6BI go from LOW to HIGH, and the LOW to HIGH on 5A/6A lags up to 100 ns from causing a LOW glitch on the 7BO1/7BO2 outputs.

[2] Open-drain input/output terminal is driven to logic LOW state by other driver.

Table 9. NMI signals

H = HIGH voltage level; L = LOW voltage level.

Input	Input/output	Output
11BI	**11A (open-drain)**	**11BO**
L	H	L
L	L[1]	H
H	L	H

[1] Open-drain input/output terminal is driven to logic LOW state by other driver.

8. Application design-in information

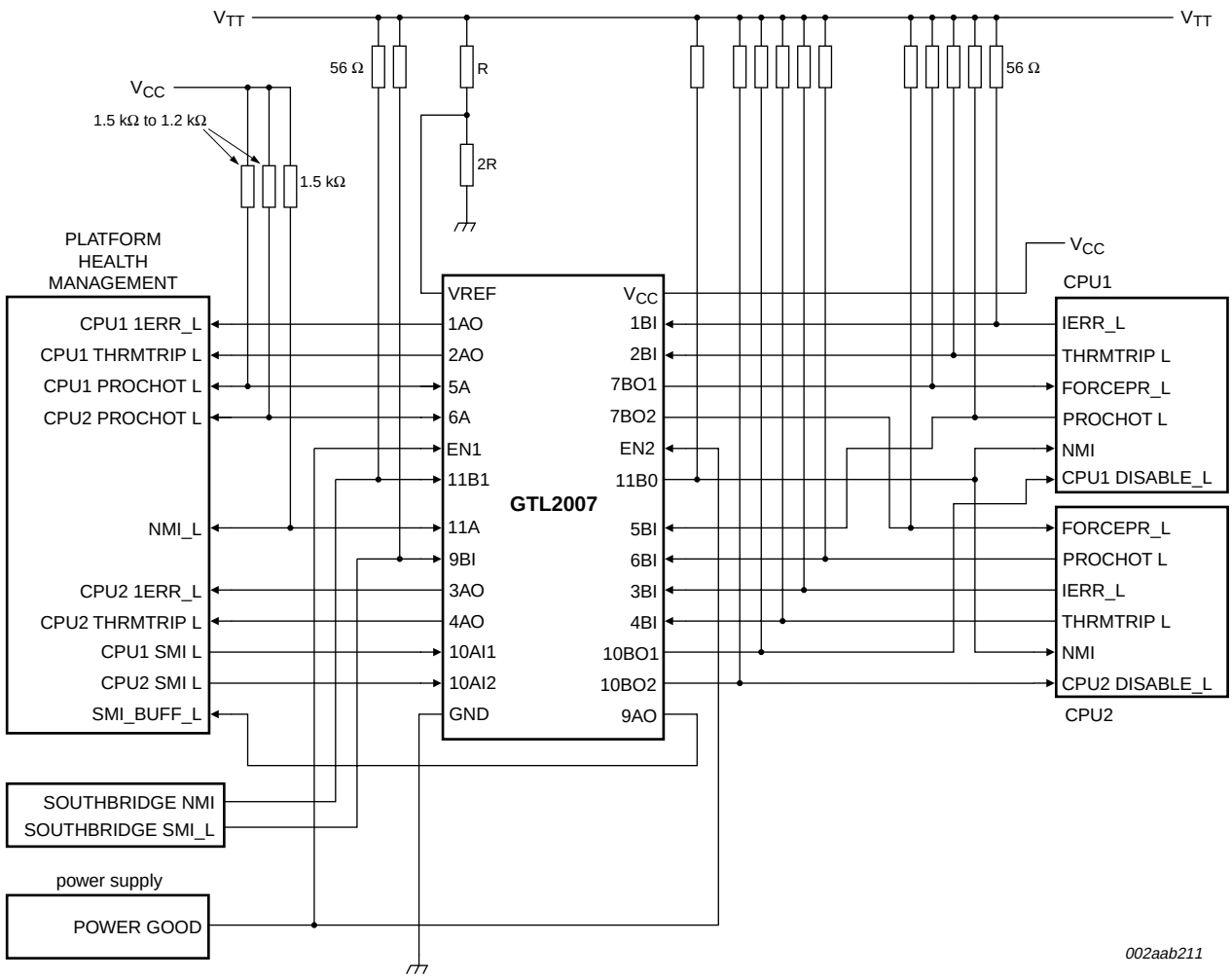


Fig 3. Typical application

9. Limiting values

Table 10. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).[1]
Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+4.6	V
I_{IK}	input clamping current	$V_I < 0$ V		-	–50	mA
V_I	input voltage	A port (LVTTL)	[2]	–0.5	+4.6	V
		B port (GTL)	[2]	–0.5	+4.6	V
I_{OK}	output clamping current	$V_O < 0$ V		-	–50	mA
V_O	output voltage	output in OFF or HIGH state; A port	[2]	–0.5	+4.6	V
		output in OFF or HIGH state; B port	[2]	–0.5	+4.6	V
I_{OL}	LOW-level output current[3]	A port		-	32	mA
		B port		-	30	mA
I_{OH}	HIGH-level output current[4]	A port		-	–32	mA
T_{stg}	storage temperature			–60	+150	°C
$T_{j(max)}$	maximum junction temperature		[5]	-	+125	°C

[1] Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under Section 10 “Recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

[2] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

[3] Current into any output in the LOW state.

[4] Current into any output in the HIGH state.

[5] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150 °C.

10. Recommended operating conditions

Table 11. Operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		3.0	3.3	3.6	V
V_{TT}	termination voltage	GTL	-	1.2	-	V
V_{ref}	reference voltage	GTL	0.64	0.8	1.1	V
V_I	input voltage	A port	0	3.3	3.6	V
		B port	0	V_{TT}	3.6	V
V_{IH}	HIGH-level input voltage	A port and ENn	2	-	-	V
		B port	V_{ref} + 0.050	-	-	V
V_{IL}	LOW-level input voltage	A port and ENn	-	-	0.8	V
		B port	-	-	V_{ref} – 0.050	V
I_{OH}	HIGH-level output current	A port	-	-	–16	mA
I_{OL}	LOW-level output current	A port	-	-	16	mA
		B port	-	-	15	mA
T_{amb}	ambient temperature	operating in free-air	–40	-	+85	°C

11. Static characteristics

Table 12. Static characteristics

Recommended operating conditions; voltages are referenced to GND (ground = 0 V). T_{amb} = −40 °C to +85 °C.

Symbol	Parameter	Conditions		Min	Typ[1]	Max	Unit
V_{OH}	HIGH-level output voltage	A port; V_{CC} = 3.0 V to 3.6 V; I_{OH} = −100 µA	[2]	V_{CC} − 0.2	3.0	-	V
		A port; V_{CC} = 3.0 V; I_{OH} = −16 mA	[2]	2.1	2.3	-	V
V_{OL}	LOW-level output voltage	A port; V_{CC} = 3.0 V; I_{OL} = 4 mA	[2]	-	0.15	0.4	V
		A port; V_{CC} = 3.0 V; I_{OL} = 8 mA	[2]	-	0.3	0.55	V
		A port; V_{CC} = 3.0 V; I_{OL} = 16 mA	[2]	-	0.6	0.8	V
		B port; V_{CC} = 3.0 V; I_{OL} = 15 mA	[2]	-	0.13	0.4	V
I_I	input current	A port; V_{CC} = 3.6 V; V_I = V_{CC}		-	-	±1	µA
		A port; V_{CC} = 3.6 V; V_I = 0 V		-	-	±1	µA
		B port; V_{CC} = 3.6 V; V_I = V_{TT} or GND		-	-	±1	µA
I_{CC}	supply current	A or B port; V_{CC} = 3.6 V; V_I = V_{CC} or GND; I_O = 0 mA		-	8	12	mA
ΔI_{CC}[3]	additional supply current	per input; A port or control inputs; V_{CC} = 3.6 V; V_I = V_{CC} − 0.6 V		-	-	500	µA
C_{io}	input/output capacitance	A port; V_O = 3.0 V or 0 V		-	2.5	3.5	pF
		B port; V_O = V_{TT} or 0 V		-	1.5	2.5	pF

[1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

[2] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[3] This is the increase in supply current for each input that is at the specified LVTTL voltage level rather than V_{CC} or GND.

12. Dynamic characteristics

Table 13. Dynamic characteristics

V_{CC} = 3.3 V ± 0.3 V.

Symbol	Parameter	Conditions		Min	Typ[1]	Max	Unit
V_{ref} = 0.73 V; V_{TT} = 1.1 V							
t_{PLH}	LOW-to-HIGH propagation delay	nA to nB; see Figure 4		1	4	8	ns
		nBI to nAO; see Figure 5		2	5.5	10	ns
		9BI to 10BOn		2	6	11	ns
		11BI to 11BO		2	8	13	ns
		5BI to 7BO1 or 6BI to 7BO2; see Figure 7		4	7	12	ns
		EN1 to nAO or EN2 to nAO; see Figure 8		2	6.5	10	ns
t_{PHL}	HIGH-to-LOW propagation delay	nA to nB; see Figure 4		2	5.5	10	ns
		nBI to nAO; see Figure 5		2	5.5	10	ns
		9BI to 10BOn		2	6	11	ns
		11BI to 11BO	[2]	2	14	21	ns
		5BI to 7BO1 or 6BI to 7BO2; see Figure 7		100	205	350	ns
		EN1 to nAO or EN2 to nAO; see Figure 8		2	6.5	10	ns
t_{PLZ}	LOW to OFF-state propagation delay	nBI to nA (I/O); see Figure 6		2	13	18	ns
		EN1 to 5A (I/O) or EN2 to 6A (I/O); see Figure 9		1	3	7	ns
t_{PZL}	OFF-state to LOW propagation delay	nBI to nA (I/O); see Figure 6		2	12	16	ns
		EN1 to 5A (I/O) or EN2 to 6A (I/O); see Figure 9		2	7	10	ns

Table 13. Dynamic characteristics *...continued*

V_{CC} = 3.3 V ± 0.3 V.

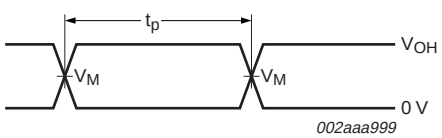
Symbol	Parameter	Conditions		Min	Typ[1]	Max	Unit
V_{ref} = 0.76 V; V_{TT} = 1.2 V							
t_{PLH}	LOW-to-HIGH propagation delay	nA to nB; see Figure 4		1	4	8	ns
		nBI to nAO; see Figure 5		2	5.5	10	ns
		9BI to 10BOn		2	6	11	ns
		11BI to 11BO		2	8	13	ns
		5BI to 7BO1 or 6BI to 7BO2; see Figure 7		4	7	12	ns
		EN1 to nAO or EN2 to nAO; see Figure 8		2	6.5	10	ns
t_{PHL}	HIGH-to-LOW propagation delay	nA to nB; see Figure 4		2	5.5	10	ns
		nBI to nAO; see Figure 5		2	5.5	10	ns
		9BI to 10BOn		2	6	11	ns
		11BI to 11BO	[2]	2	14	21	ns
		5BI to 7BO1 or 6BI to 7BO2; see Figure 7		100	205	350	ns
		EN1 to nAO or EN2 to nAO; see Figure 8		2	6.5	10	ns
t_{PLZ}	LOW to OFF-state propagation delay	nBI to nA (I/O); see Figure 6		2	13	18	ns
		EN1 to 5A (I/O) or EN2 to 6A (I/O); see Figure 9		1	3	7	ns
t_{PZL}	OFF-state to LOW propagation delay	nBI to nA (I/O); see Figure 6		2	12	16	ns
		EN1 to 5A (I/O) or EN2 to 6A (I/O); see Figure 9		2	7	10	ns

[1] All typical values are at V_{CC} = 3.3 V and T_{amb} = 25 °C.

[2] Includes ~7.6 ns RC rise time of test load pull-up on 11A, 1.5 kΩ pull-up and 21 pF load on 11A has about 23 ns RC rise time.

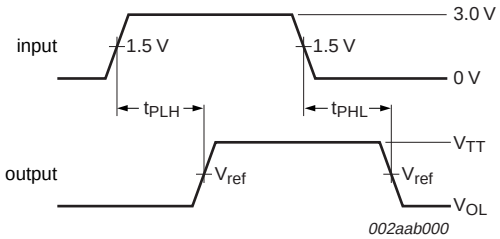
12.1 Waveforms

V_M = 1.5 V at $V_{CC} \geq$ 3.0 V for A ports; $V_M = V_{ref}$ for B ports.



V_M = 3.0 V for A port and V_{TT} for B port

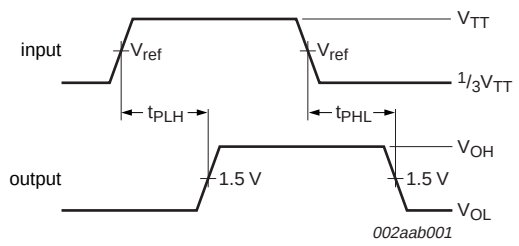
a. Pulse duration



A port to B port

b. Propagation delay times

Fig 4. Voltage waveforms



PRR ≤ 10 MHz; Z_O = 50 Ω; t_r ≤ 2.5 ns; t_f ≤ 2.5 ns

Fig 5. Propagation delay, nBI to nAO

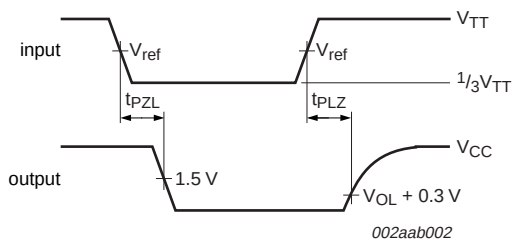


Fig 6. nBI to nA (I/O)

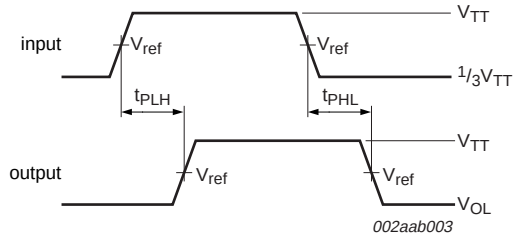


Fig 7. 5BI to 7BO1 or 6BI to 7BO2

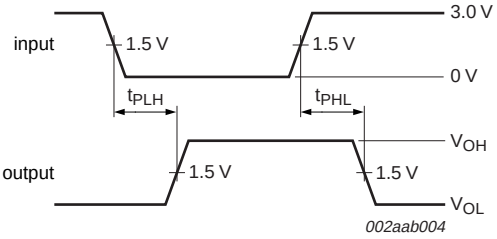


Fig 8. EN1 to nAO or EN2 to nAO

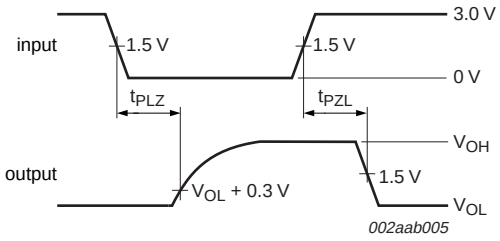


Fig 9. EN1 to 5A (I/O) or EN2 to 6A (I/O)

13. Test information

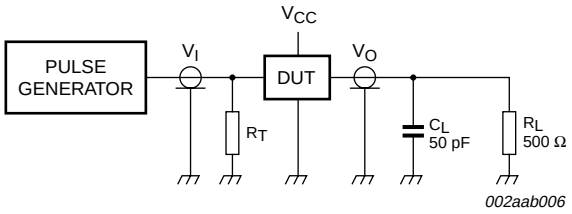


Fig 10. Load circuit for A outputs

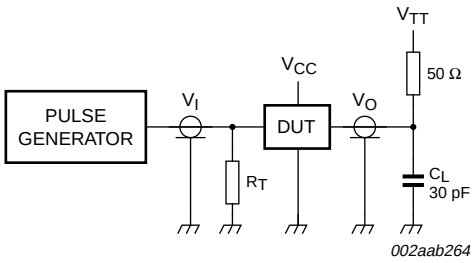
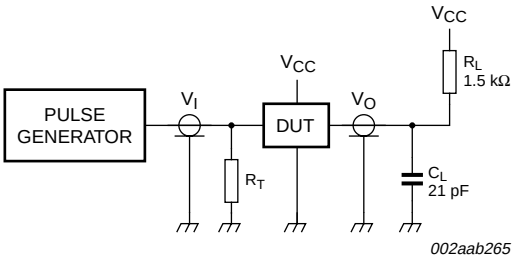


Fig 11. Load circuit for B outputs



R_L = load resistor.

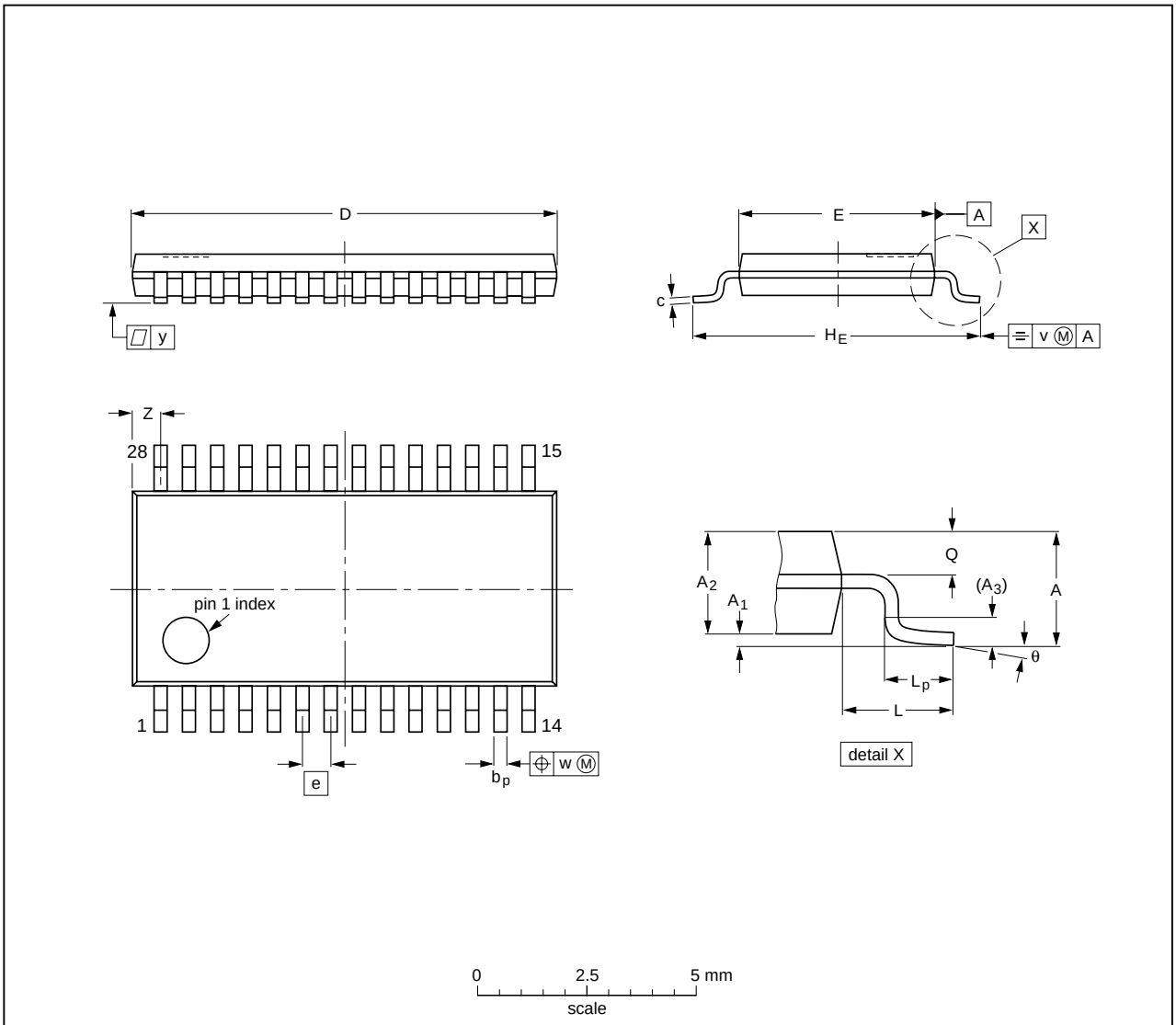
C_L = load capacitance; includes jig and probe capacitance.

R_T = termination resistance; should be equal to Z_o of pulse generators.

Fig 12. Load circuit for open-drain LVTTL I/O

14. Package outline

TSSOP28: plastic thin shrink small outline package; 28 leads; body width 4.4 mm **SOT361-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	9.8 9.6	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.8 0.5	8^o 0^o

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT361-1		MO-153				~~99-12-27~~ 03-02-19

Fig 13. Package outline SOT361-1 (TSSOP28)

15. Soldering

This text provides a very brief insight into a complex technology. A more in-depth account of soldering ICs can be found in Application Note *AN10365 "Surface mount reflow soldering description"*.

15.1 Introduction to soldering

Soldering is one of the most common methods through which packages are attached to Printed Circuit Boards (PCBs), to form electrical circuits. The soldered joint provides both the mechanical and the electrical connection. There is no single soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and Surface Mount Devices (SMDs) are mixed on one printed wiring board; however, it is not suitable for fine pitch SMDs. Reflow soldering is ideal for the small pitches and high densities that come with increased miniaturization.

15.2 Wave and reflow soldering

Wave soldering is a joining technology in which the joints are made by solder coming from a standing wave of liquid solder. The wave soldering process is suitable for the following:

- Through-hole components
- Leaded or leadless SMDs, which are glued to the surface of the printed circuit board

Not all SMDs can be wave soldered. Packages with solder balls, and some leadless packages which have solder lands underneath the body, cannot be wave soldered. Also, leaded SMDs with leads having a pitch smaller than ~0.6 mm cannot be wave soldered, due to an increased probability of bridging.

The reflow soldering process involves applying solder paste to a board, followed by component placement and exposure to a temperature profile. Leaded packages, packages with solder balls, and leadless packages are all reflow solderable.

Key characteristics in both wave and reflow soldering are:

- Board specifications, including the board finish, solder masks and vias
- Package footprints, including solder thieves and orientation
- The moisture sensitivity level of the packages
- Package placement
- Inspection and repair
- Lead-free soldering versus PbSn soldering

15.3 Wave soldering

Key characteristics in wave soldering are:

- Process issues, such as application of adhesive and flux, clinching of leads, board transport, the solder wave parameters, and the time during which components are exposed to the wave
- Solder bath specifications, including temperature and impurities

15.4 Reflow soldering

Key characteristics in reflow soldering are:

- Lead-free versus SnPb soldering; note that a lead-free reflow process usually leads to higher minimum peak temperatures (see Figure 14) than a PbSn process, thus reducing the process window
- Solder paste printing issues including smearing, release, and adjusting the process window for a mix of large and small components on one board
- Reflow temperature profile; this profile includes preheat, reflow (in which the board is heated to the peak temperature) and cooling down. It is imperative that the peak temperature is high enough for the solder to make reliable solder joints (a solder paste characteristic). In addition, the peak temperature must be low enough that the packages and/or boards are not damaged. The peak temperature of the package depends on package thickness and volume and is classified in accordance with Table 14 and 15

Table 14. SnPb eutectic process (from J-STD-020C)

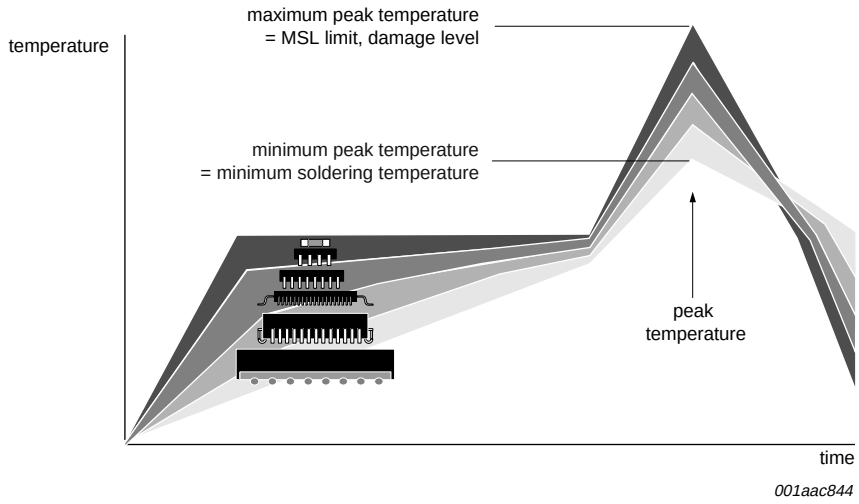
Package thickness (mm)	Package reflow temperature (°C)	
	Volume (mm^3)	
	< 350	≥ 350
< 2.5	235	220
≥ 2.5	220	220

Table 15. Lead-free process (from J-STD-020C)

Package thickness (mm)	Package reflow temperature (°C)		
	Volume (mm^3)		
	< 350	350 to 2000	> 2000
< 1.6	260	260	260
1.6 to 2.5	260	250	245
> 2.5	250	245	245

Moisture sensitivity precautions, as indicated on the packing, must be respected at all times.

Studies have shown that small packages reach higher temperatures during reflow soldering, see Figure 14.



MSL: Moisture Sensitivity Level

Fig 14. Temperature profiles for large and small components

For further information on temperature profiles, refer to Application Note *AN10365 "Surface mount reflow soldering description"*.

16. Abbreviations

Table 16. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Silicon
CPU	Central Processing Unit
DUT	Device Under Test
ESD	Electrostatic Discharge
GTL	Gunning Transceiver Logic
HBM	Human Body Model
LVTTL	Low Voltage Transistor-Transistor Logic
MM	Machine Model
PRR	Pulse Rate Repetition
TTL	Transistor-Transistor Logic
VRD	Voltage Regulator Down

17. Revision history

Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
GTL2007_2	20070216	Product data sheet	-	GTL2007_1
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Data sheet descriptive title changed from “13-bit GTL to LVTTL translator with power good control” to “12-bit GTL to LVTTL translator with power good control” • Section 1 “General description”: – 4th paragraph re-written – deleted (old) 5th paragraph • Section 2 “Features”: added (new) 2nd bullet item • Figure 1 “Logic diagram of GTL2007”: updated symbols to IEC convention • Figure 3 “Typical application” modified: – in blocks CPU1 and CPU2, changed “SMI L” to “DISABLE_L” – in block PLATFORM HEALTH MANAGEMENT: changed “CPU2 IERR_L” to “CPU2 1ERR_L” • Table 10 “Limiting values”: parameter definitions updated; added Table note 3 and Table note 4 • Table 13 “Dynamic characteristics”: data reorganized (no specification changed) • Table 16 “Abbreviations”: added “DUT”			
GTL2007_1 (9397 750 13264)	20050602	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Date of release: 16 February 2007
Document identifier: GTL2007_2